Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) Method for making a thin layer starting from a wafer comprising a front face divided into surface elements and with a given relief, and a back face, comprising steps consisting of:

a) obtaining a support handle with a face acting as a bonding face;

b) preparing the front face of the wafer, this preparation including incomplete planarisation of the front face of the wafer, to obtain a bonding energy E_0 with the bonding face of the support handle, between a first value corresponding to the minimum bonding energy compatible with the later thinning step, and a second value corresponding to the maximum bonding energy compatible with the subsequent desolidarisation operation, the bonding energy E_0 being such that $E_0 = \alpha.E$, where E is the bonding energy that would be obtained if the front face of the wafer was completely planarised, α is the ratio between the incompletely planarised surface of the front face of the wafer and the surface of the front face of the wafer if it were completely planarised;

c) solidarising the front face of the wafer on the bonding face of the support handle, by direct bonding;

d) thinning the wafer starting from its back face until the thin layer is obtained;

e) transferring the surface elements from the thin layer onto a usage support, involving separation from the support handle.

2. (Original) Method according to claim 1, wherein α is between 0.4 and 0.8.

3. (Original) Method according to claim 1, wherein all surface elements are transferred onto the usage support in step e).

4. (Original) Method according to claim 1, wherein surface elements are transferred individually in step e), step b) is carried out so as to obtain a bonding energy E_0 for each surface element, step e) being preceded by a step in which the thin layer is cut into surface elements.

5. (Original) Method according to claim 1, wherein surface elements are transferred by groups of surface elements in step e), step b) is carried out so as to obtain a bonding energy E_0 for each group of surface elements, step e) being preceded by a step in which the thin layer is cut into groups of surface elements.

6. (Original) Method according to claim 4, wherein the support handle is cut at the same time as the thin layer is cut.

7. (Previously presented) Method according to claim 4, wherein the cutting step is made by combining a deep etching step of the thin layer and a sawing step.

8. (Original) Method according to claim 1, wherein the part of the wafer from which the thin layer will be obtained includes semiconducting material.

9. (Original) Method according to claim 8, wherein the surface elements are composed of complete or incomplete electronic components.

10. (Original) Method according to claim 1, wherein in step b), the incomplete planarisation is done by a mechanical-chemical polishing method.

11. (Original) Method according to claim 1, wherein in step d), the wafer is thinned by a mechanical, chemical or mechanical-chemical thinning method.

12. (Original) Method according to claim 1, wherein in step e), separation from the support handle is achieved particularly by mechanical and / or pneumatic means.

13. (Original) Method according to claim 1, wherein in step e), the transfer takes place before separation from the support handle.

14. (Previously presented) Method according to claim 5, wherein the cutting step is made by combining a deep etching step of the thin layer and a sawing step.

15. (Newly added) Method for making a thin layer starting from a wafer comprising a front face divided into surface elements and with a given relief, and a back face, comprising steps consisting of:

a) obtaining a support handle with a face acting as a bonding face;

b) preparing the front face of the wafer, this preparation including incomplete planarisation of the front face of the wafer, to obtain a bonding energy E_0 with the bonding face of the support handle, between a first value corresponding to the minimum bonding energy compatible with the later thinning step, and a second value corresponding to the maximum

bonding energy compatible with the subsequent desolidarisation operation, the bonding energy E_0 being such that $E_0 = \alpha.E$, where E is the bonding energy that would be obtained if the front face of the wafer was completely planarised, α is the ratio between the incompletely planarised surface of the front face of the wafer and the surface of the front face of the wafer if it were completely planarised, wherein α is between 0.4 and 0.8;

c) solidarising the front face of the wafer on the bonding face of the support handle, by direct bonding;

d) thinning the wafer starting from its back face until the thin layer is obtained;

e) transferring the surface elements from the thin layer onto a usage support, involving separation from the support handle.

16. (Newly added) Method according to claim 15, wherein all surface elements are transferred onto the usage support in step e).

17. (Newly added) Method according to claim 15, wherein surface elements are transferred individually in step e), step b) is carried out so as to obtain a bonding energy E_0 for each surface element, step e) being preceded by a step in which the thin layer is cut into surface elements.

18. (Newly added) Method according to claim 15, wherein surface elements are transferred by groups of surface elements in step e), step b) is carried out so as to obtain a bonding energy E_0 for each group of surface elements, step e) being preceded by a step in which the thin layer is cut into groups of surface elements.

19. (Newly added) Method according to claim 18, wherein the support handle is cut at the same time as the thin layer is cut.

20. (Newly added) Method according claim 18, wherein the cutting step is made by combining a deep etching step of the thin layer and a sawing step.

21. (Newly added) Method according to claim 15, wherein the part of the wafer from which the thin layer will be obtained includes semiconducting material.

22. (Newly added) Method according to claim 21, wherein the surface elements are composed of complete or incomplete electronic components.

23. (Newly added) Method according to claim 15, wherein in step b), the incomplete planarisation is done by a mechanical-chemical polishing method.

24. (Newly added) Method according to claim 15, wherein in step d), the wafer is thinned by a mechanical, chemical or mechanical-chemical thinning method.

25. (Newly added) Method according to claim 15, wherein in step e), separation from the support handle is achieved particularly by mechanical and / or pneumatic means.

26. (Newly added) Method according to claim 15, wherein in step e), the transfer takes place before separation from the support handle.

27. (Newly added) Method according to claim 19, wherein the cutting step is made by combining a deep etching step of the thin layer and a sawing step.